

IN THE CLAIMS:

Please amend claim 21 as follows:

LISTING OF CURRENT CLAIMS

Claim 1 (Previously Presented). A light emitting diode comprising:
a light emitting structure having a plurality of light emitting layers which generate light in responsive to an injection current;
a transparent conductive oxide layer formed on said light emitting structure,
5 said transparent conductive oxide layer having one of a metal grid and a dot pattern formed therein and abutting said light emitting structure;
a metal reflective layer formed on said transparent conductive oxide layer, said transparent conductive oxide layer being formed to prevent said metal reflective layer from reacting with said light emitting layers while annealing for improving ohmic
10 contact of electrodes of said light emitting diode; and
a conductive base substrate formed on said metal reflective layer.

Claim 2. (Original) The light emitting diode according to claim 1, wherein said conductive base structure is selected from the group consisting of copper, aluminum, SiC, AlN and silicon.

Claim 3. (Original) The light emitting diode according to claim 1, wherein the transparent conductive oxide layer is selected from the group consisting In_2O_3 , SnO_2 , CdO , ZnO , ITO, CTO, CuAlO_2 , CuGaO_2 and SrCu_2O_2 .

Claim 4. (Original) The light emitting diode according to claim 1, wherein said metal reflective layer is selected from the group consisting of Au, Al and Ag.

Claim 5. (Original) The light emitting diode according to claim 1, further comprising a metal bonding layer formed in between said conductive base substrate and said metal reflective layer.

Claim 6. (Original) The light emitting diode according to claim 5, wherein said bonding layer is selected from the group consisting of In, Au-Sn alloy, Au-Si alloy, Pb-Sn alloy and Au-Ge alloy, PdIn.

Claim 7. (Original) The light emitting diode according to claim 5, further comprising a diffusion barrier layer formed in between said metal reflective layer and said metal bonding layer.

Claim 8. (Original) The light emitting diode according to claim 7, wherein said diffusion barrier layer is selected from the group consisting of conductive oxide layer, refractory metal layer, and refractory metal silicide.

Claim 9. (Previously Presented) A light emitting diode comprising:

a conductive base substrate;

a light emitting structure having a plurality of light emitting layers which generate light in responsive to an injection current;

5 a transparent conductive oxide layer formed on said light emitting structure, said transparent conductive oxide layer having one of an ohmic contact metal grid and a dot patterned layer formed therein and atop said light emitting structure;

10 a metal reflective layer formed on said transparent conductive oxide layer, said transparent conductive oxide layer being formed to prevent said metal reflective layer from reacting with said light emitting layers while annealing for improving ohmic contact of electrodes of said light emitting diode;

a diffusion barrier layer formed in between said metal reflective layer and a metal bonding layer; and

15 said metal bonding layer formed in between said conductive base substrate and said diffusion barrier layer so as to bond said conductive base substrate and said light emitting structure.

Claim 10. (Original) The light emitting diode according to claim 9, wherein said conductive base substrate is a heat dissipation and electrical conductive layer selected from the group consisting of copper, aluminum, SiC, AlN and silicon.

Claim 11. (Original) The light emitting diode according to claim 9, wherein said transparent conductive layer is selected from the group consisting of In_2O_3 , SnO_2 , CdO, ZnO, ITO, CTO, CuAlO_2 , CuGaO_2 and SrCu_2O_2 .

Claim 12. (Original) The light emitting diode according to claim 9, wherein said metal reflective layer is selected from the group consisting of Au, Al and Ag.

Claim 13. (Original) The light emitting diode according to claim 9, wherein said metal bonding layer is selected from the group consisting of In, Au-Sn alloy, Au-Si alloy, Pb-Sn alloy and Au-Ge alloy, PdIn.

Claim 14. (Canceled)

Claim 15. (Previously Presented) The light emitting diode according to claim 9, wherein said diffusion barrier layer is selected from the group consisting of conductive oxide layer, refractory metal layer, and refractory metal silicide.

Claims 16-19. (Canceled)

Claim 20. (Previously Presented) A light emitting diode comprising:
a conductive base substrate;
a light emitting structure, having a plurality of light emitting layers which
5 generate light in responsive to injection current;
a transparent ohmic contact metal layer formed on a top layer of said light
emitting layers;
a transparent conductive oxide layer formed on said transparent ohmic
contact metal layer;
10 a metal reflective layer formed on said transparent conductive oxide layer;
and
a metal bonding layer formed in between said conductive base substrate and
said metal reflective layer so as to bond said conductive base substrate together
with said light emitting structure.

21. (Currently Amended) The light emitting diode according to claim ~~19~~ 20
wherein said transparent ohmic contact metal layer is a Ni/Au double layer.